

SOT23 SILICON DUAL VARIABLE CAPACITANCE DIODE

ZDC833A

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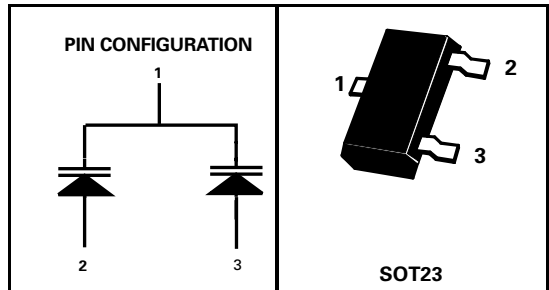
FEATURES

- * VHF to UHF operation
- * Common Cathode Dual Diode
- * Monolithic construction

APPLICATIONS

- * Mobile radios and Pagers
- * Cellular telephones
- * Voltage controlled Crystal Oscillators

PARTMARKING DETAIL ZDC833A – C2A



ABSOLUTE MAXIMUM RATINGS.(Each Diode)

PARAMETER	SYMBOL	VALUE	UNIT
Forward Current	I_F	200	mA
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$). (Each Diode)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Reverse Breakdown Voltage	V_{BR}	25			V	$I_R = 10\mu\text{A}$
Reverse Leakage Current	I_R		0.2	10	nA	$V_R = 20\text{V}$
Temperature Coefficient	η			400	ppm/ $^{\circ}\text{C}$	$V_R = 3\text{V}$, $f=1\text{MHz}$
Diode Capacitance	C_d	29.7	33	36.3	pF	$V_R = 2\text{V}$, $f=1\text{MHz}$
Capacitance Ratio	C_d / C_d	5.0		6.5		$V_R = 2\text{V}/20\text{V}$, $f=1\text{MHz}$
Figure of Merit	Q	200				$V_R = 3\text{V}$, $f=50\text{MHz}$

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TYPICAL CHARACTERISTICS

